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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE


Appl. No. : 10/647,985 Confirmation No. 3087
Applicant: : Patricia Beauregard Smith, et al.
Filed: : August 26, 2003
Art Unit: : 1746
Examiner: : Zeinab El-Arini

Docket No. : TI-33260
Customer No. : 23494

INFORMATION DISCLOSURE STATEMENT UNDER 37 CFR 1.97 & 1.98

Commissioner For Patents
P.O. Box 1450
Alexandria, VA 22313-1450

MAILING CERTIFICATE UNDER 37 C.F.R. § 1.8(a)
I hereby certify that the above correspondence is being deposited with the U.S. Postal Service with sufficient postage as First Class Mail in an envelope addressed to: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450 on 1-19-06.


Ann Trent

Dear Sir:

Applicants wish to bring to the attention of the Patent and Trademark Office the information noted on the enclosed PTO/SB/08A.

In accordance with 37 CFR 1.97 (d), this Information Disclosure Statement is being submitted before payment of the issue fee and is accompanied by the following certification specified in 37 CFR 1.97 (e).

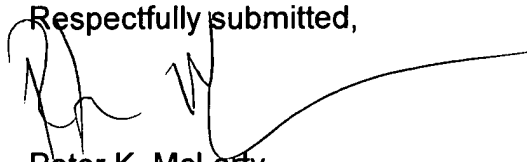
On information and belief, I hereby certify that each item of information contained in this Information Disclosure Statement was cited in a communication from a foreign patent office in a counterpart foreign application not more than three months prior to the filing of this statement.

Pursuant to 37 CFR 1.97 (d), Applicants respectfully petition that this Information Disclosure Statement be considered by the Examiner.

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Please charge any shortage in the fees due in connection with the filing of this paper, including extension of time fees, to the deposit account of Texas Instruments Incorporated, Account No. 20-0668, and please credit any excess fees to such Deposit Account.

Respectfully submitted,

A handwritten signature in black ink, appearing to read 'Peter K. McLarty', with a long horizontal flourish extending to the right.

Peter K. McLarty
Attorney for Applicants
Reg. No. 44,923

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PTO/SB/08A (08-00)

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INFORMATION DISCLOSURE STATEMENT BY APPLICANT

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Complete If Known

Application Number	10/647,985
Filing Date	August 26, 2003
First Named Inventor	Patricia Beauregard Smith, et al.
Group Art Unit	1746
Examiner Name	Zeinab El-Arini
Attorney Docket No.	TI-33260

U.S. PATENT DOCUMENTS

Exam. Initials*	Cite No. ¹	U.S. Patent Document		Name of Patentee or Applicant of Cited Doc.	Date of Pub. of Cited Doc. (mm-dd-yyyy)	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number	Kind Code ² (if known)			
	AA	2003/0104320	A1	Nguyen et al.	06/05/2003	
	AB	2003/0008518	A1	Chang et al.	01/09/2003	
	AC	6,107,202		Chiu et al.	08/22/2000	
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	AF	5,643,407		Chang	07/01/1997	
	AG					
	AH					
	AI					
	AJ					

FOREIGN PATENT DOCUMENTS

Exam. Initials*	Cite No. ¹	Foreign Patent Document			Name of Patentee or Applicant of Cited Doc.	Date of Pub. of Cited Doc. (mm-dd-yyyy)	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ⁶
		Office ³	Number ⁴	Kind Code ² (if known)				
	BA							
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NON PATENT LITERATURE DOCUMENTS

Exam. Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
	CA	OKUDA, Seichiro, et al., "New Dry Tool after Cleaning of Low-k Dielectrics," <i>Solid State Phenomena</i> , Vol. 92, 2003, pp. 287-291, Proceedings of Ultra Clean Processing of Silicon Surfaces Conference, April 15, 2003, Diffusion and Defect Data, Solid State Data, Part B, Vaduz, LI, September 2003.	
	CB	YANG, S.C., et al., "Process Optimization of Hydrogen Silsesquioxane (HSQ) Via Etch for 0.18um Technology and Beyond," Advanced Metallization Conference 1999, Orlando, Florida, September 28-30, 1999, pp. 455-459.	
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Examiner Signature	Date Considered
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*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

¹Unique citation designation number. ²Applicant is to place a check mark here if English Translation is attached.